DATA SHEET

BF245A; BF245B; BF245C
N-channel silicon field-effect transistors

Product specification
Supersedes data of April 1995

1996 Jul 30

N-channel silicon field-effect transistors

BF245A; BF245B; BF245C

FEATURES

- Interchangeability of drain and source connections
- Frequencies up to 700 MHz.

APPLICATIONS

- LF, HF and DC amplifiers.

DESCRIPTION

General purpose N-channel symmetrical junction field-effect transistors in a plastic TO-92 variant package.

CAUTION
The device is supplied in an antistatic package. The gate-source input must be protected against static discharge during transport or handling.

PINNING

PIN	SYMBOL	DESCRIPTION
1	d	drain
2	s	source
3	g	gate

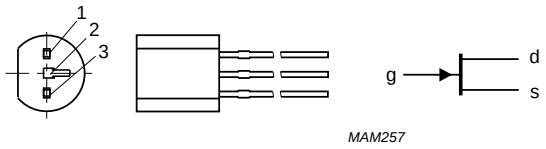


Fig.1 Simplified outline (TO-92 variant) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{DS}	drain-source voltage		–	–	±30	V
V_{GSoff}	gate-source cut-off voltage	I_D = 10 nA; V_{DS} = 15 V	–0.25	–	–8	V
V_{GSO}	gate-source voltage	open drain	–	–	–30	V
I_{DSS}	drain current	V_{DS} = 15 V; V_{GS} = 0				
	BF245A		2	–	6.5	mA
	BF245B		6	–	15	mA
	BF245C		12	–	25	mA
P_{tot}	total power dissipation	T_{amb} = 75 °C	–	–	300	mW
$\lvert y_{fs} \rvert$	forward transfer admittance	V_{DS} = 15 V; V_{GS} = 0; f = 1 kHz; T_{amb} = 25 °C	3	–	6.5	mS
C_{rs}	reverse transfer capacitance	V_{DS} = 20 V; V_{GS} = –1 V; f = 1 MHz; T_{amb} = 25 °C	–	1.1	–	pF

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	drain-source voltage		–	±30	V
V_{GDO}	gate-drain voltage	open source	–	−30	V
V_{GSO}	gate-source voltage	open drain	–	−30	V
I_D	drain current		–	25	mA
I_G	gate current		–	10	mA
P_{tot}	total power dissipation	up to T_{amb} = 75 °C;	–	300	mW
		up to T_{amb} = 90 °C; note 1	–	300	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	operating junction temperature		–	150	°C

Note

1. Device mounted on a printed-circuit board, minimum lead length 3 mm, mounting pad for drain lead minimum 10 mm × 10 mm.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	in free air	250	K/W
	thermal resistance from junction to ambient		200	K/W

STATIC CHARACTERISTICS

T_j = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{(BR)GSS}$	gate-source breakdown voltage	I_G = −1 μA; V_{DS} = 0	−30	–	V
V_{GSoff}	gate-source cut-off voltage	I_D = 10 nA; V_{DS} = 15 V	−0.25	−8.0	V
V_{GS}	gate-source voltage	I_D = 200 μA; V_{DS} = 15 V			
	BF245A		−0.4	−2.2	V
	BF245B		−1.6	−3.8	V
	BF245C		−3.2	−7.5	V
I_{DSS}	drain current	V_{DS} = 15 V; V_{GS} = 0; note 1			
	BF245A		2	6.5	mA
	BF245B		6	15	mA
	BF245C		12	25	mA
I_{GSS}	gate cut-off current	V_{GS} = −20 V; V_{DS} = 0	–	−5	nA
		V_{GS} = −20 V; V_{DS} = 0; T_j = 125 °C	–	−0.5	μA

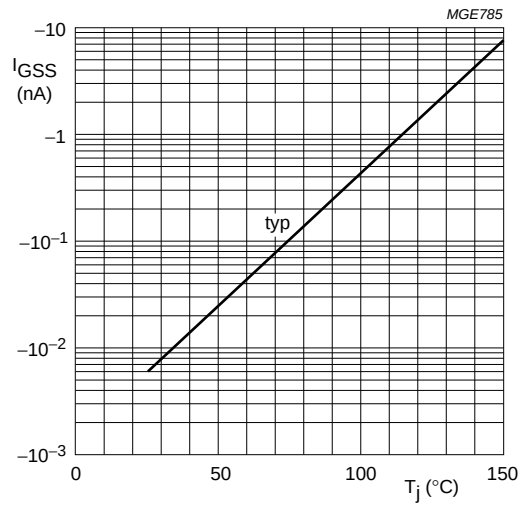
Note

1. Measured under pulse conditions: t_p = 300 μs; $\delta \leq 0.02$.

DYNAMIC CHARACTERISTICS

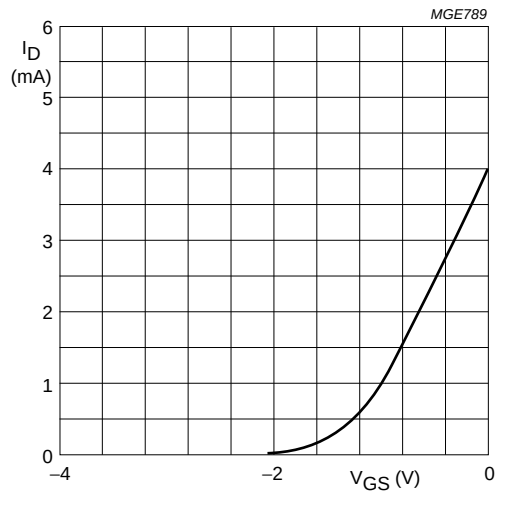
Common source; T_{amb} = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
C_{is}	input capacitance	V_{DS} = 20 V; V_{GS} = −1 V; f = 1 MHz	–	4	–	pF
C_{rs}	reverse transfer capacitance	V_{DS} = 20 V; V_{GS} = −1 V; f = 1 MHz	–	1.1	–	pF
C_{os}	output capacitance	V_{DS} = 20 V; V_{GS} = −1 V; f = 1 MHz	–	1.6	–	pF
g_{is}	input conductance	V_{DS} = 15 V; V_{GS} = 0; f = 200 MHz	–	250	–	μS
g_{os}	output conductance	V_{DS} = 15 V; V_{GS} = 0; f = 200 MHz	–	40	–	μS
$\lvert y_{fs} \rvert$	forward transfer admittance	V_{DS} = 15 V; V_{GS} = 0; f = 1 kHz	3	–	6.5	mS
		V_{DS} = 15 V; V_{GS} = 0; f = 200 MHz	–	6	–	mS
$\lvert y_{rs} \rvert$	reverse transfer admittance	V_{DS} = 15 V; V_{GS} = 0; f = 200 MHz	–	1.4	–	mS
$\lvert y_{os} \rvert$	output admittance	V_{DS} = 15 V; V_{GS} = 0; f = 1 kHz	–	25	–	μS
f_{gfs}	cut-off frequency	V_{DS} = 15 V; V_{GS} = 0; g_{fs} = 0.7 of its value at 1 kHz	–	700	–	MHz
F	noise figure	V_{DS} = 15 V; V_{GS} = 0; f = 100 MHz; R_G = 1 kΩ (common source); input tuned to minimum noise	–	1.5	–	dB



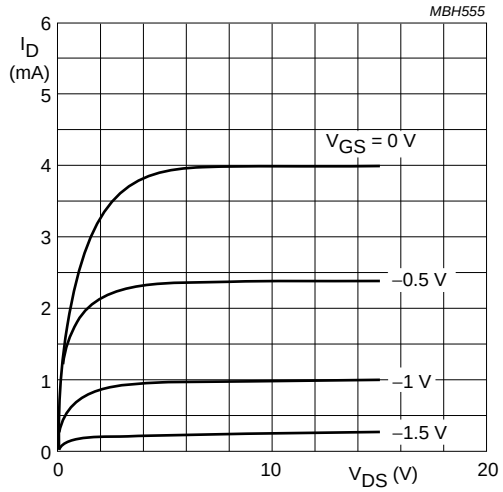
V_{DS} = 0; V_{GS} = −20 V.

Fig.2 Gate leakage current as a function of junction temperature; typical values.



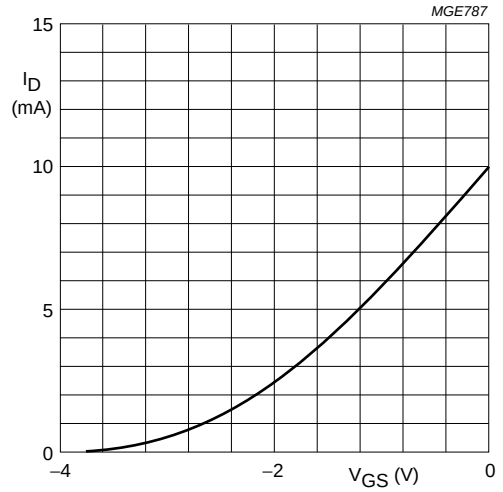
V_{DS} = 15 V; T_j = 25 °C.

Fig.3 Transfer characteristics for BF245A; typical values.



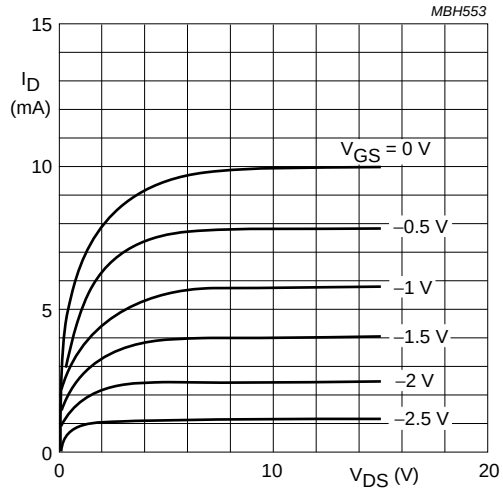
V_{DS} = 15 V; T_j = 25 °C.

Fig.4 Output characteristics for BF245A; typical values.



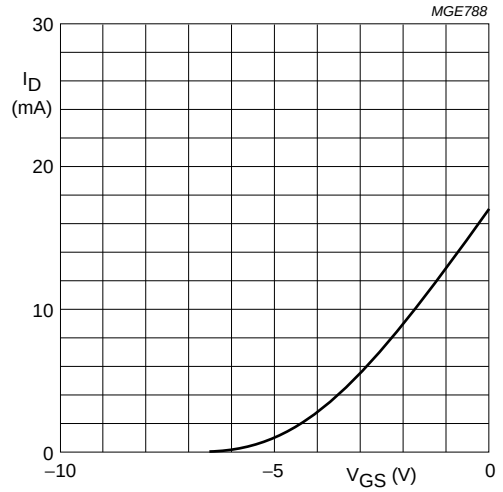
V_{DS} = 15 V; T_j = 25 °C.

Fig.5 Transfer characteristics for BF245B; typical values.



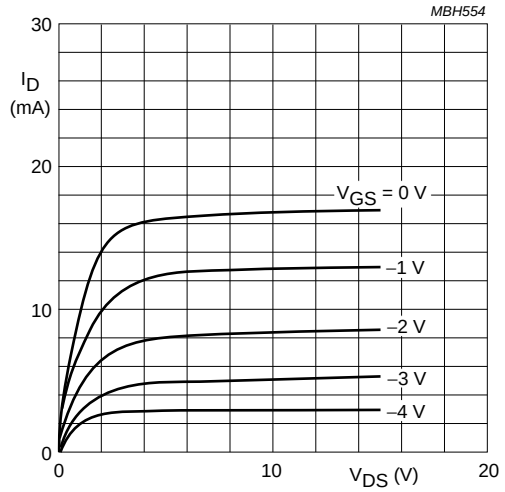
V_{DS} = 15 V; T_j = 25 °C.

Fig.6 Output characteristics for BF245B; typical values.



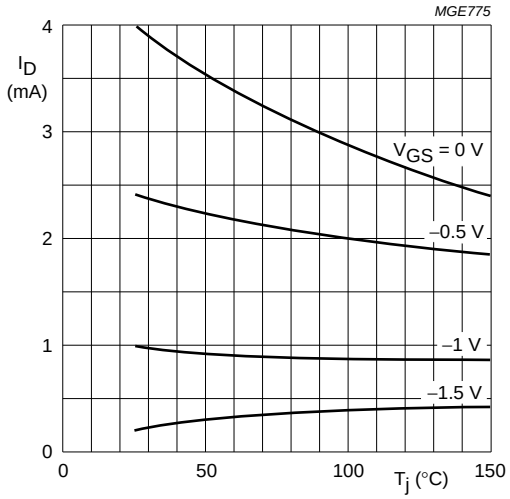
V_{DS} = 15 V; T_j = 25 °C.

Fig.7 Transfer characteristics for BF245C; typical values.



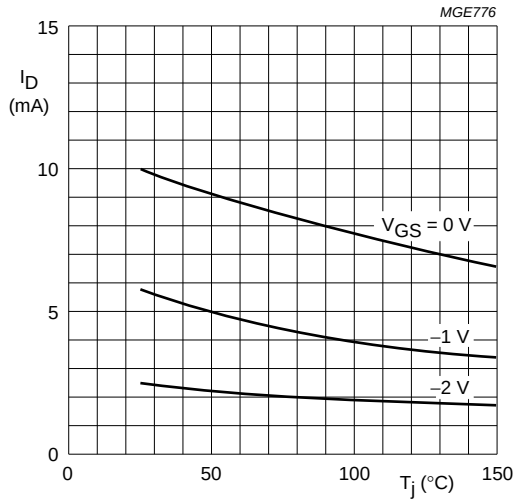
V_{DS} = 15 V; T_j = 25 °C.

Fig.8 Output characteristics for BF245C; typical values.



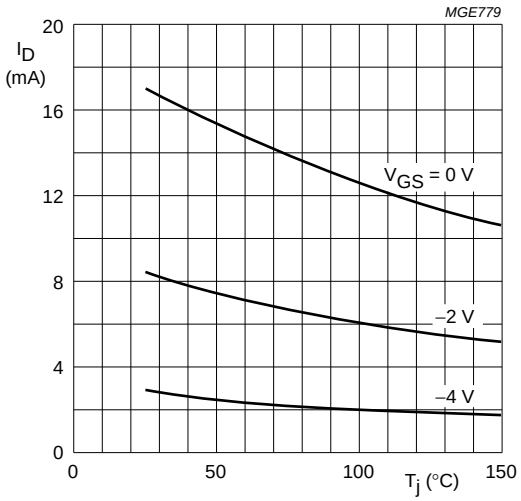
V_{DS} = 15 V.

Fig.9 Drain current as a function of junction temperature; typical values for BF245A.



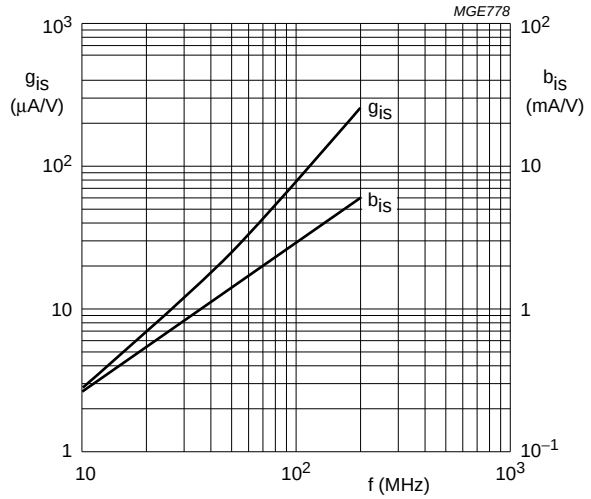
V_{DS} = 15 V.

Fig.10 Drain current as a function of junction temperature; typical values for BF245B.



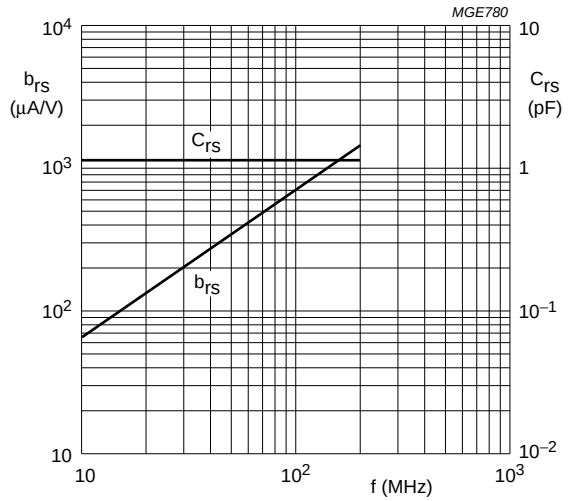
V_{DS} = 15 V.

Fig.11 Drain current as a function of junction temperature; typical values for BF245C.



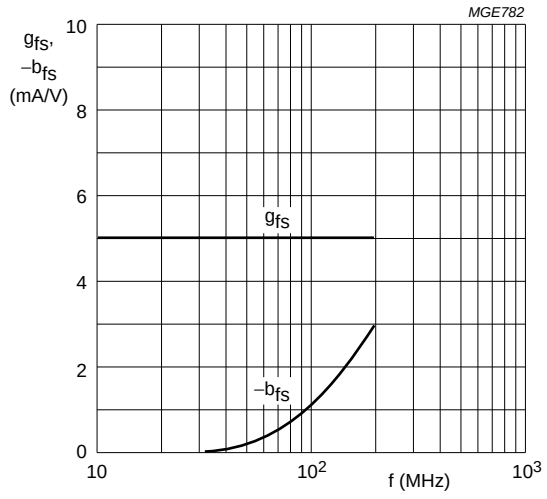
V_{DS} = 15 V; V_{GS} = 0; T_{amb} = 25 °C.

Fig.12 Input admittance; typical values.



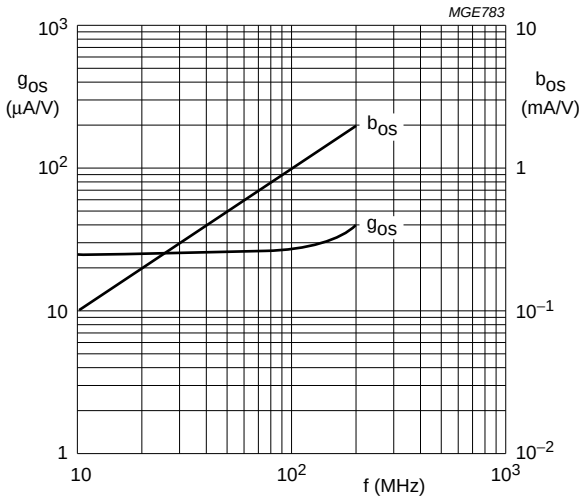
V_{DS} = 15 V; V_{GS} = 0; T_{amb} = 25 °C.

Fig.13 Common source reverse admittance as a function of frequency; typical values.



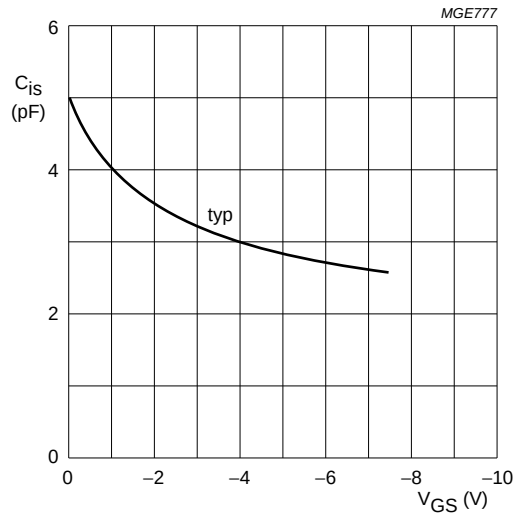
V_{DS} = 15 V; V_{GS} = 0; T_{amb} = 25 °C.

Fig.14 Common-source forward transfer admittance as a function of frequency; typical values.



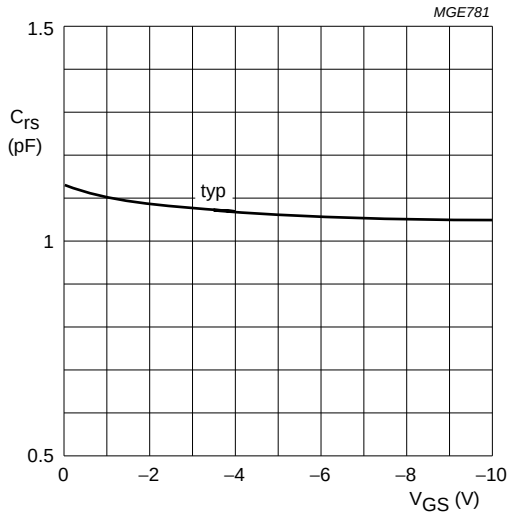
V_{DS} = 15 V; V_{GS} = 0; T_{amb} = 25 °C.

Fig.15 Common-source output admittance as a function of frequency; typical values.



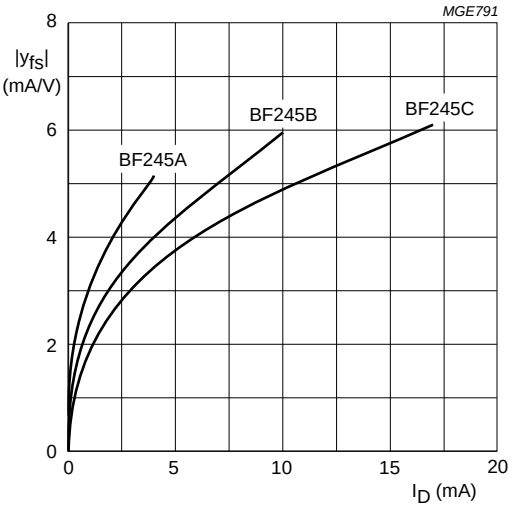
V_{DS} = 20 V; f = 1 MHz; T_{amb} = 25 °C.

Fig.16 Input capacitance as a function of gate-source voltage; typical values.



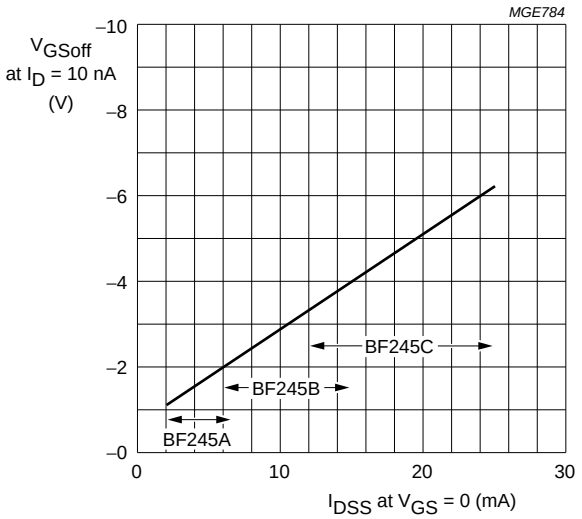
V_{DS} = 20 V; f = 1 MHz; T_{amb} = 25 °C.

Fig.17 Reverse transfer capacitance as a function of gate-source voltage; typical values.



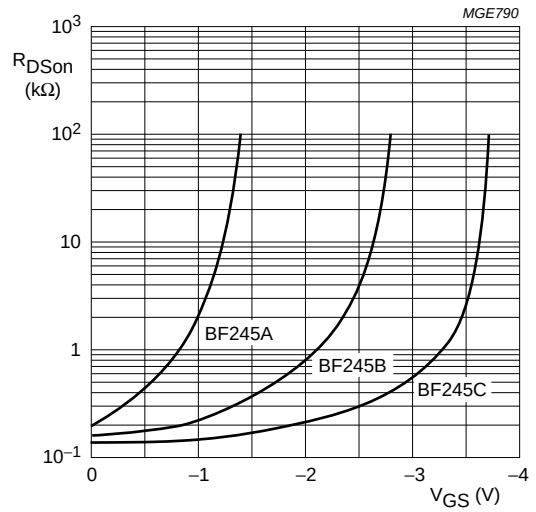
V_{DS} = 15 V; f = 1 kHz; T_{amb} = 25 °C.

Fig.18 Forward transfer admittance as a function of drain current; typical values.



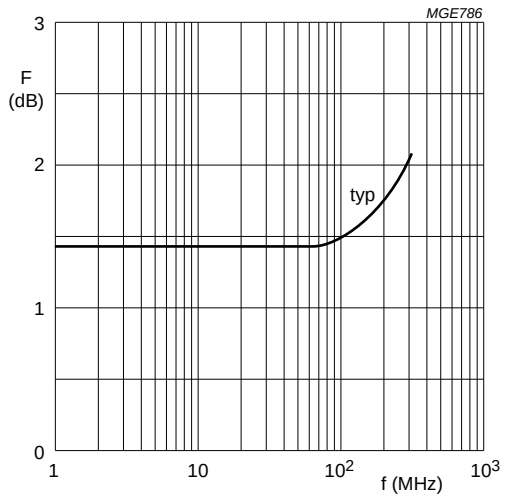
V_{DS} = 15 V; T_j = 25 °C.

Fig.19 Gate-source cut-off voltage as a function of drain current; typical values.



V_{DS} = 0; f = 1 kHz; T_{amb} = 25 °C.

Fig.20 Drain-source on-state resistance as a function of gate-source voltage; typical values.

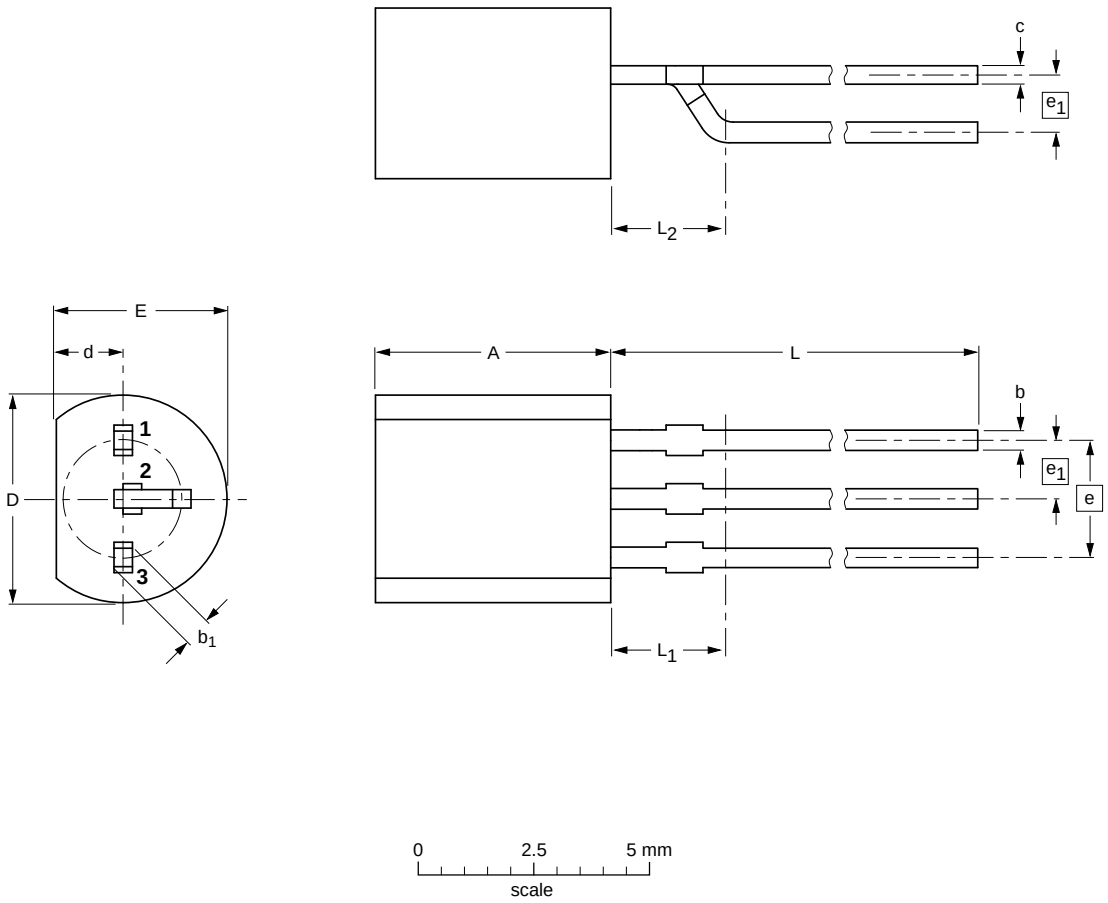


V_{DS} = 15 V; V_{GS} = 0; R_G = 1 kΩ; T_{amb} = 25 °C.
Input tuned to minimum noise.

Fig.21 Noise figure as a function of frequency; typical values.

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads (on-circle) **SOT54 variant**



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b_1	c	D	d	E	e	e_1	L	L_1 (1) max	L_2 max
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT54 variant						~~04-06-28~~ 05-01-10

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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